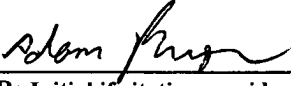


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EXAMINER INITIAL	DOCUMENT NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
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	DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	Translation YES NO	
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<i>AP</i>	"Cu Dual Damascene Integration Issues" by S. Kordic et al., 1999 Proc. 16 th Intl VLSI Multilevel Interconn. Conf. (VMIC), Sept. 7-9, 1999, pp. 53-62						
<i>AP</i>	"Aluminum Persists as Copper Age Dawns" by A. E. Brown, Semi. Intl., August 1999, pp. 58-66						
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